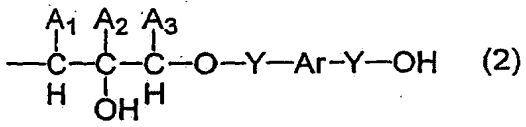
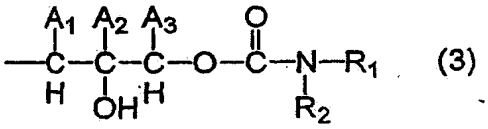
Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

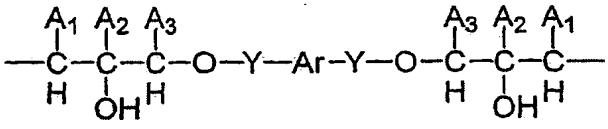
1. (Currently Amended) A composition for forming anti-reflective coating characterized in that the composition comprises a triazine trione compound having hydroxyalkyl structure as substituent on nitrogen atom, a triazine trione oligomer compound having hydroxyalkyl structure as substituent on nitrogen atom, or a triazine trione polymer compound having hydroxyalkyl structure as substituent on nitrogen atom; wherein the triazine trione compound having hydroxyalkyl structure as substituent on nitrogen atom, the triazine trione oligomer compound having hydroxyalkyl structure as substituent on nitrogen atom, or the triazine trione polymer compound having hydroxyalkyl structure as substituent on nitrogen atom is a triazine trione compound having a substituent of formula (2) or (3) as substituent on nitrogen atom, or a triazine trione oligomer compound or triazine trione polymer compound having a structure in which at least two triazine trione rings are linked through a linking group of formula (4) or (5) on the nitrogen atoms:



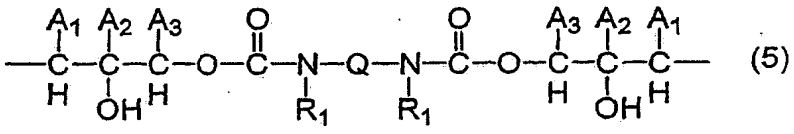
(2)



(3)



(4)

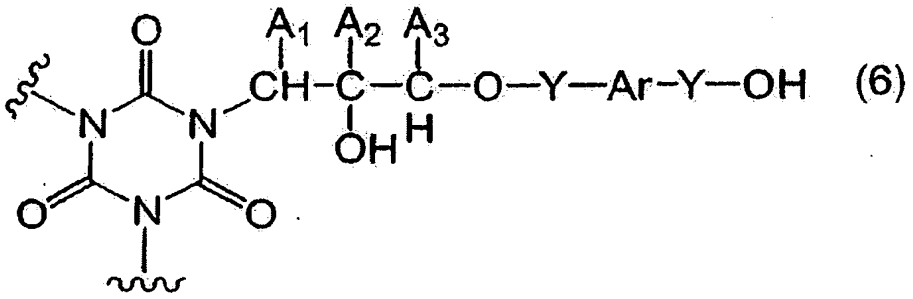


(5)

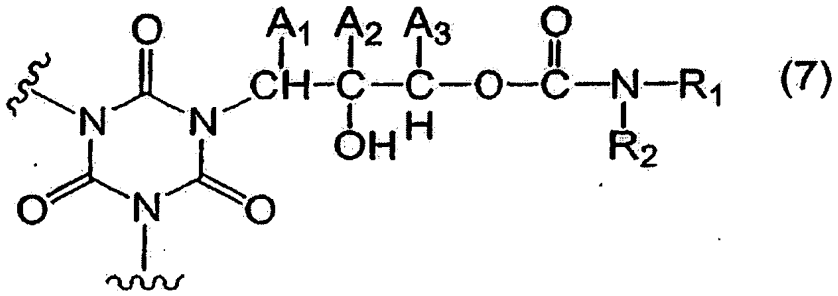
wherein A_1, A_2 and A_3 are independently of one another hydrogen atom, methyl or ethyl, each Y is independently a direct bond or -C(=O)-, Ar is benzene ring or naphthalene ring which may be substituted with C_{1-6} alkyl, phenyl, naphthyl, halogen atom, C_{1-6} alkoxycarbonyl, nitro, carboxy, cyano, C_{1-6} alkoxy, hydroxy, thiol, C_{1-6} alkylthio or amino, Q is C_{1-6} alkyl, C_{5-8} cycloalkyl, Ar or $-CH_2-Ar-CH_2-$, R_1 is C_{1-6} alkyl, phenyl or benzyl, R_2 is hydrogen atom, C_{1-6} alkyl, phenyl or benzyl.

2-3. (Canceled)

4. (Currently Amended) The composition for forming anti-reflective coating according to ~~claim 3,~~ claim 1, wherein the triazine trione compound having a substituent of formula (2) or (3) has a structure of formula (6) or (7):



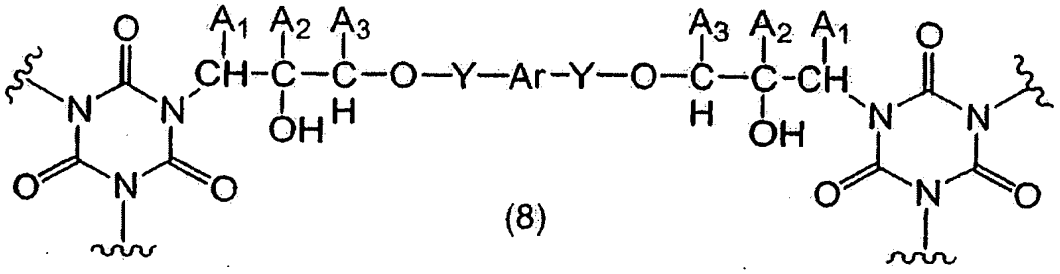
(6)



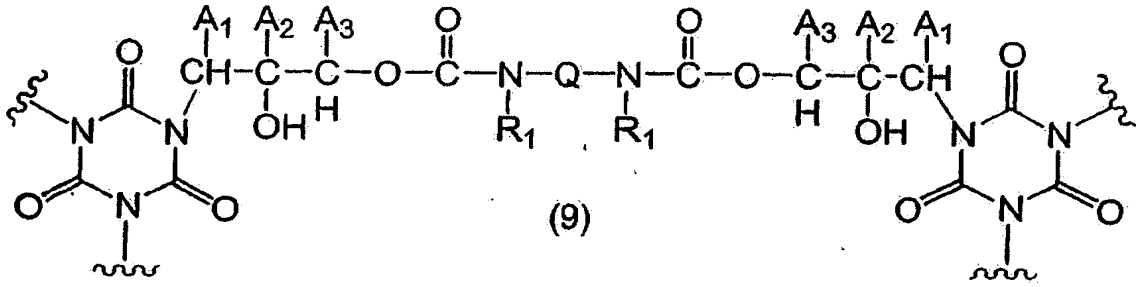
(7)

5. (Currently Amended) The composition for forming anti-reflective coating according to ~~claim 3,~~ claim 1, wherein the triazine trione oligomer compound or triazine trione polymer

compound having a structure in which at least two triazine trione rings are linked through a linking group of formula (4) or (5) on the nitrogen atoms has a structure of formula (8) or (9):

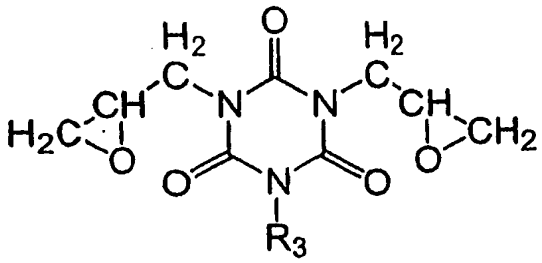


(8)

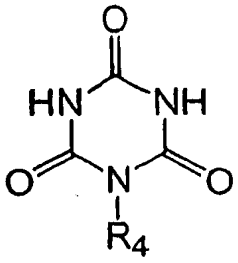


(9)

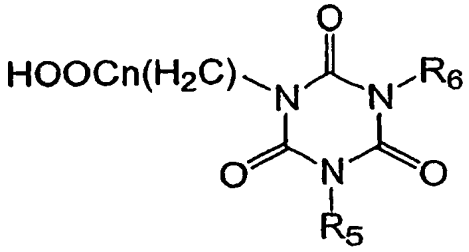
6. (Currently Amended) ~~The composition~~ A composition for forming anti-reflective coating characterized in that the composition comprises a triazine trione compound having hydroxyalkyl structure as substituent on nitrogen atom, a triazine trione oligomer compound having hydroxyalkyl structure as substituent on nitrogen atom, or a triazine trione polymer compound having hydroxyalkyl structure as substituent on nitrogen atom; and ~~for forming anti-reflective coating according to claim 1,~~ wherein the triazine trione oligomer compound having hydroxyalkyl structure as substituent on nitrogen atom, or triazine trione polymer compound having hydroxyalkyl structure as substituent on nitrogen atom is a reaction product of a compound of formula (10) with a compound of formula (11) or (12):



(10)



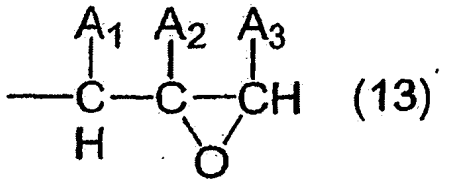
(11)



(12)

wherein R_3 is C_{1-6} alkyl, C_{3-6} alkenyl, phenyl, benzyl or 2,3-epoxypropyl, R_4 and R_5 are C_{1-6} alkyl, C_{3-6} alkenyl, phenyl or benzyl, R_6 is C_{1-6} alkyl, phenyl, benzyl or $-(CH_2)_nCOOH$, and n is a number of 1, 2 or 3.

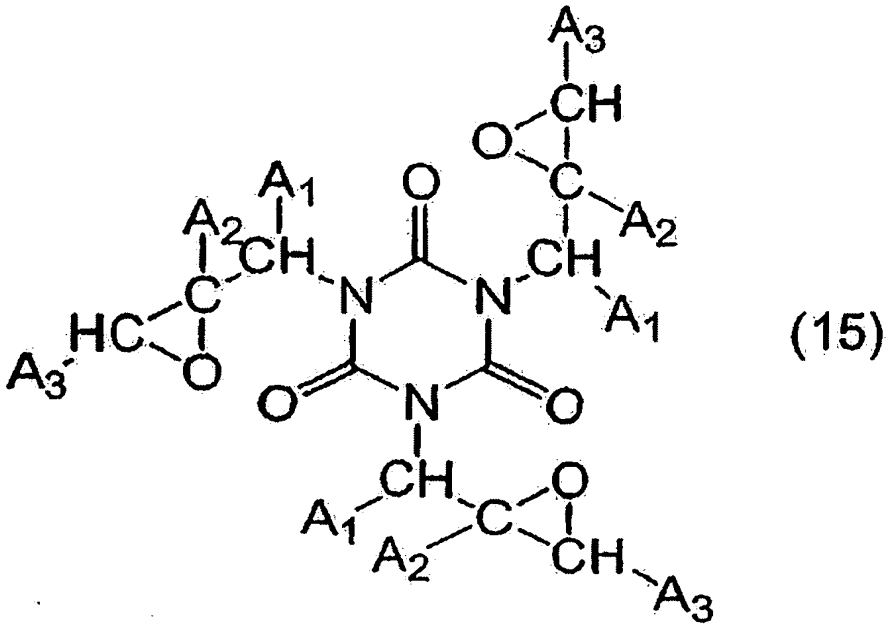
7. (Currently Amended) The composition for forming anti-reflective coating according to ~~claim 3,~~ claim 1, wherein the triazine trione compound having a substituent of formula (2) as substituent on nitrogen atom, or the triazine trione oligomer compound or triazine trione polymer compound having a structure in which at least two triazine trione rings are linked through a linking group of formula (4) on the nitrogen atoms is produced from a triazine trione compound having at least two nitrogen atoms having a substituent of formula (13) on nitrogen atom and a phenyl compound or naphthalene compound of formula (14) having at least two substituents selected from carboxy and hydroxy which are identical or different from each other



(13)

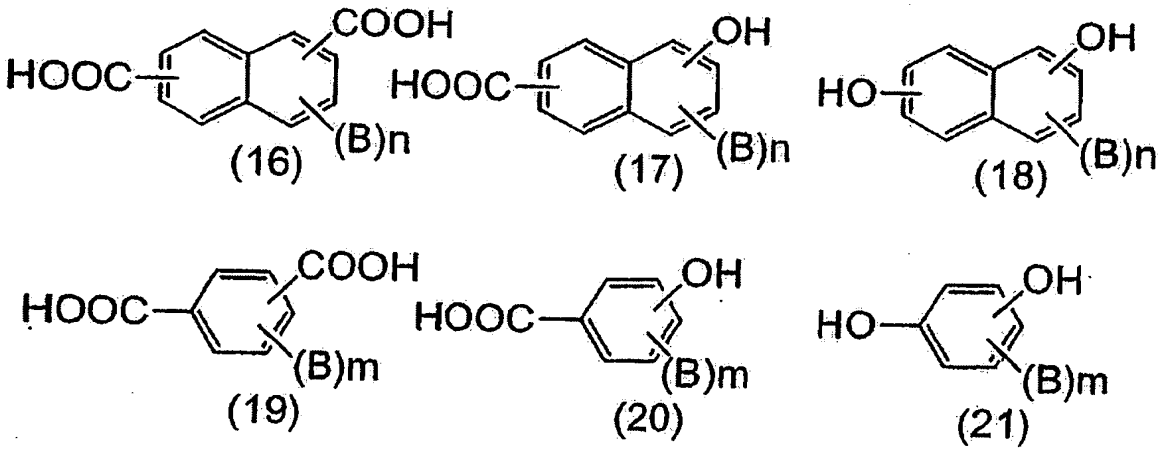
(14)

8. (Previously Presented) The composition for forming anti-reflective coating according to claim 7, wherein triazine trione compound having at least two nitrogen atoms having a substituent of formula (13) on nitrogen atom is a triazine trione compound of formula (15)



(15)

9. (Previously Presented) The composition for forming anti-reflective coating according to claim 7, wherein the phenyl compound or naphthalene compound of formula (14) is at least one compound selected from the group consisting of compounds of formulae (16) to (21)



wherein B is hydrogen atom, C_{1-6} alkyl, phenyl, naphthyl, halogen atom, C_{1-6} alkoxycarbonyl, nitro, carboxy, cyano, C_{1-6} alkoxy, hydroxy, thiol, C_{1-6} alkylthio or amino, n is a number of 1 to 6, m is a number of 1 to 4, and B may be identical with or different from each other in case where n or m is 2 or more.

10. (Previously Presented) The composition for forming anti-reflective coating according to claim 1, further containing a crosslinking agent having at least two crosslink-forming substituents.

11. (Previously Presented) The composition for forming anti-reflective coating according to claim 1, further containing an acid and/or an acid generator.

12. (Previously Presented) The composition for forming anti-reflective coating according to claim 1, further containing a resin having at least one crosslinking-forming substituent selected from hydroxy, carboxy, amino and thiol.

13. (Previously Presented) An anti-reflective coating produced by coating the composition for forming anti-reflective coating according to claim 1 on a semiconductor substrate, and baking it, wherein the anti-reflective coating has an attenuation coefficient k to a light at a wavelength of 248 nm ranging from 0.40 to 0.65.

14. (Previously Presented) An anti-reflective coating produced by coating the

composition for forming anti-reflective coating according to claim 1 on a semiconductor substrate, and baking it, wherein the anti-reflective coating has an attenuation coefficient k to a light at a wavelength of 157 nm ranging from 0.20 to 0.50.

15. (Previously Presented) An anti-reflective coating produced by coating the composition for forming anti-reflective coating according to claim 1 on a semiconductor substrate, and baking it, wherein the anti-reflective coating has an attenuation coefficient k to a light at a wavelength of 193 nm ranging from 0.20 to 0.60.

16. (Previously Presented) A method of forming an anti-reflective coating for use in a manufacture of a semiconductor device, comprising the steps of: coating the composition for forming anti-reflective coating according to claim 1 on a substrate, and baking it.

17. (Previously Presented) A method of forming an anti-reflective coating for use in a manufacture of a semiconductor device by use of a light of wavelength 248 nm, 193 nm or 157 nm, comprising the steps of: coating the composition for forming anti-reflective coating according to claim 1 on a substrate, and baking it.

18. (Previously Presented) A method of forming a photoresist pattern for use in a manufacture of a semiconductor device comprising the steps of:

coating the composition for forming anti-reflective coating according to claim 1 on a semiconductor substrate and baking it to form an anti-reflective coating,

forming a photoresist layer on the anti-reflective coating,

exposing the semiconductor substrate covered with the anti-reflective coating and the photoresist layer with a light, and

developing the exposed photoresist layer.

19. (Original) The method of forming a photoresist pattern according to claim 18, wherein the exposure is carried out with a light of wavelength 248 nm, 193 nm or 157 nm.